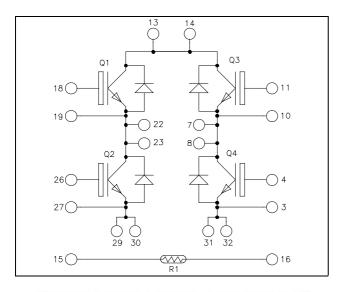
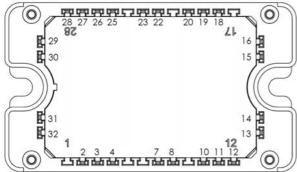


Full bridge Trench + Field Stop IGBT4 Power module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

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$V_{CES} = 1200V$ $I_{C} = 90A$ @ $T_{c} = 80^{\circ}C$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

• Trench + Field Stop IGBT 4

- Low voltage drop
- Low leakage current
- Low switching losses
- Low leakage current
- RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter	Max ratings	Unit	
V _{CES}	Collector - Emitter Voltage		1200	V
т	Continuous Collector Current	$T_c = 25^{\circ}C$	110	
Ic	Continuous Collector Current	$T_c = 80^{\circ}C$	90	Α
I _{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Power Dissipation	$T_c = 25^{\circ}C$	385	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	150A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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Power Matters.*

Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.85	2.25	V
V _{CE(sat)}		$I_{\rm C} = 75 A$	$T_j = 150^{\circ}C$		2.25		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3mA$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			4.4		
Coes	Output Capacitance				0.29		nF
C _{res}	Reverse Transfer Capacitance				0.24		
Q _G	Gate charge	$V_{GE}=\pm 15V$; $V_{CE}=600V$ $I_{C}=75A$			0.57		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			130		
Tr	Rise Time	$V_{GE} = \pm 15V$			20		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 75A$			300		ns
T _f	Fall Time	$R_G = 2.2\Omega$			45		
T _{d(on)}	Turn-on Delay Time	$ Inductive Switching (150°C) V_{GE} = \pm 15V V_{Bus} = 600V I_C = 75A R_G = 2.2\Omega $			150		
Tr	Rise Time				35		ns
T _{d(off)}	Turn-off Delay Time				350		no
$T_{\rm f}$	Fall Time				80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		3.4		mJ
Lon	Turn-on Switching Energy	$V_{Bus} = 600V$	$T_J = 150^{\circ}C$		8.5		1115
E _{off}	Turn-off Switching Energy	$I_C = 75A$	$T_J = 25^{\circ}C$		4.2		mJ
L'011	Turn on Switching Energy	$R_G = 2.2\Omega$	$T_{\rm J} = 150^{\circ}{\rm C}$		7.2		1115
I _{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 900V$ $t_p \le 10\mu s$; $T_i = 150^{\circ}C$			300		А
R _{thJC}	Junction to Case Thermal Resistance					0.39	°C/W

Reverse diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions			Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			150	μΑ
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		70		Α
$V_{\rm F}$	Diode Forward Voltage	$I_F = 75A$	$T_j = 25^{\circ}C$		1.7	2.2	V
v F		$V_{GE} = 0V$	$T_j = 150^{\circ}C$		1.65		v
t	Reverse Recovery Time	$I_{\rm p} = 75$ Å	$T_j = 25^{\circ}C$		155		ns
t _{rr}	Reverse Recovery Time		$T_j = 150^{\circ}C$		300		115
0	Pavara Pacavary Charge		$T_j = 25^{\circ}C$		7.3		
Qn	Reverse Recovery Charge		$T_j = 150^{\circ}C$		15.2		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		2.6		mJ
			$T_j = 150^{\circ}C$		5.5		IIIJ
R_{thJC}	Junction to Case Thermal Resistance					0.62	°C/W



Power Matters."

Thermal and package characteristics

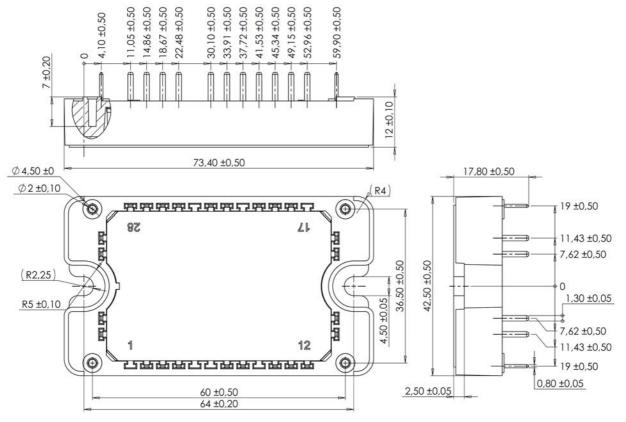
Symbol	Characteristic			Min	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
TJ	Operating junction temperature range			-40	175	
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T _{STG}	Storage Temperature Range			-40	125	C
T _C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		$T_C=100^{\circ}C$		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
$$R_{T}: \text{ Thermistor value at T}$$

Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

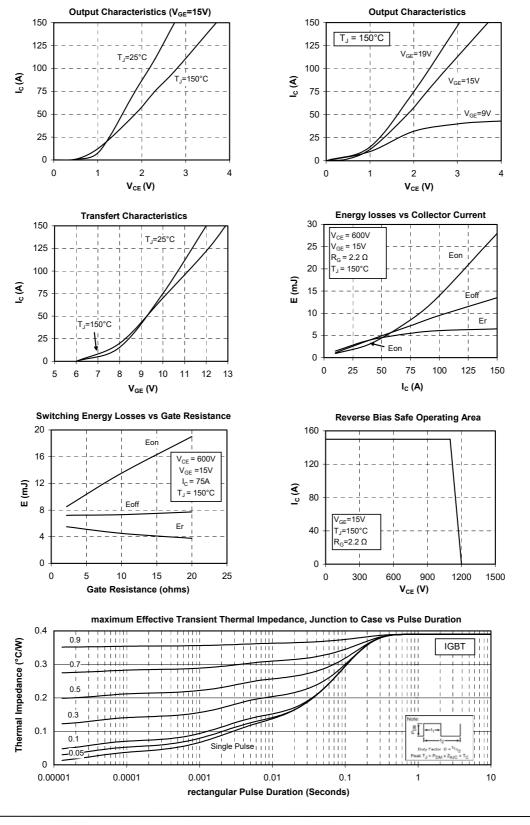
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Fower matters

Typical Performance Curve



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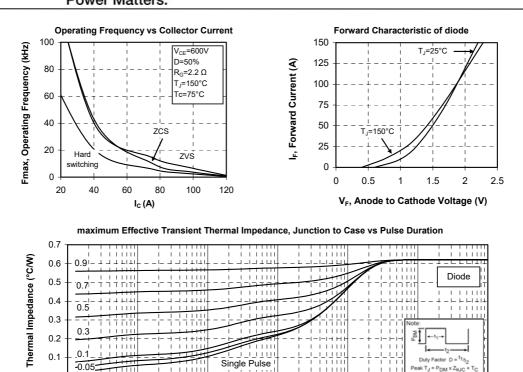
0.0001

APTGL90H120T3G

ik T = PDM × Z₀,

10

1



0.001 0.01 0.1 **Rectangular Pulse Duration in Seconds**

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